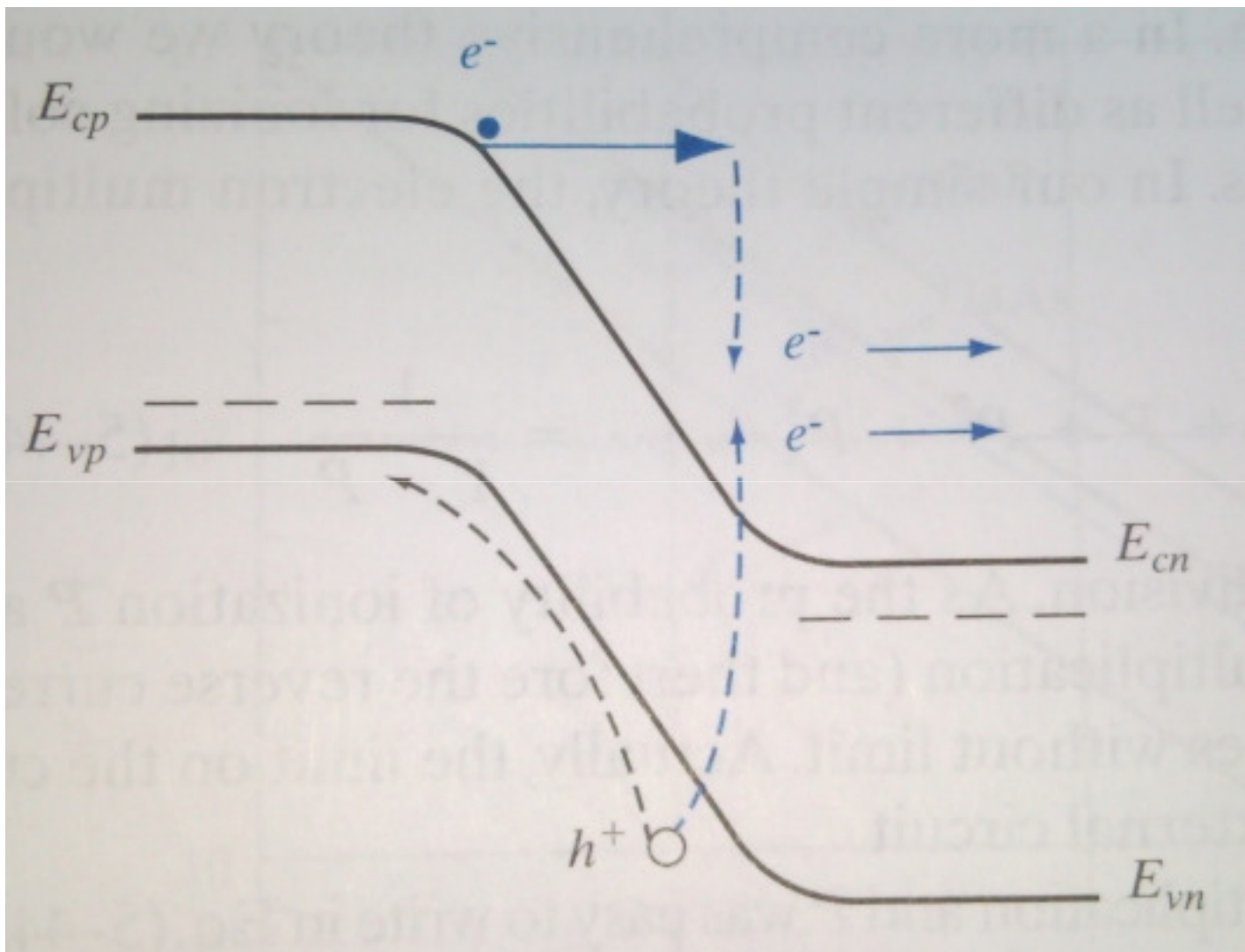


¹²The dissipated power (IV) in the junction is, of course, greater for a given current in the breakdown regime than it would be for the forward bias, simply because V is greater.



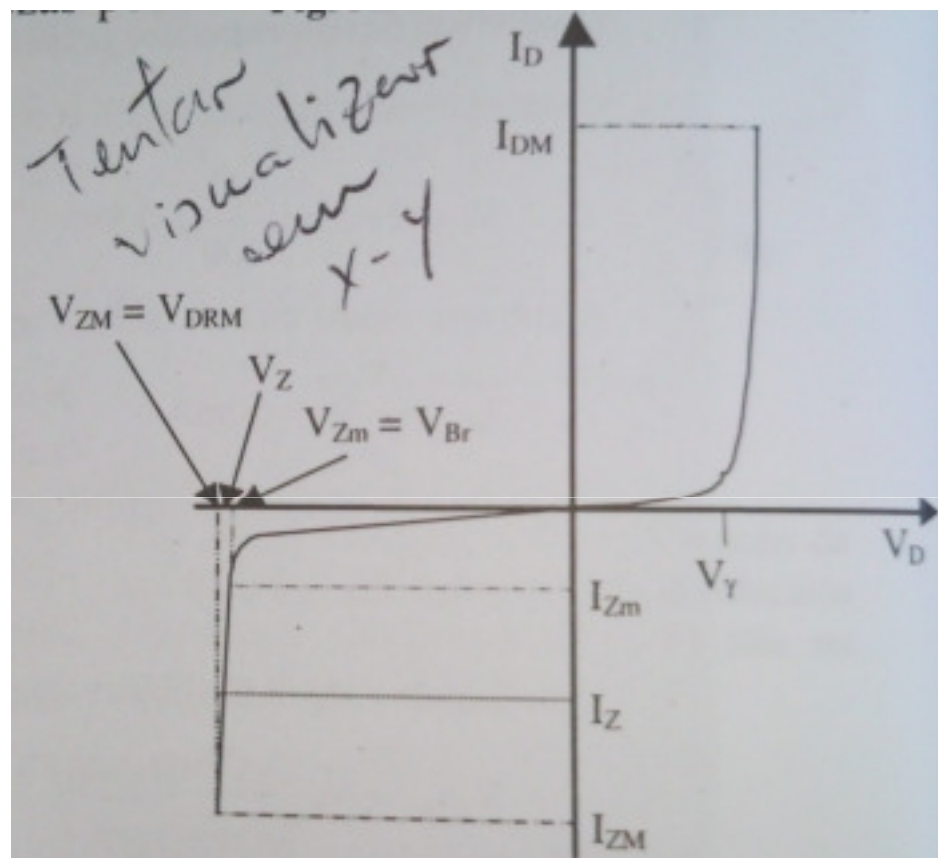


Fig. 3.28 - Curva característica de um diodo zener.

Fig. 3.30 - Modelo para um diodo zener real.

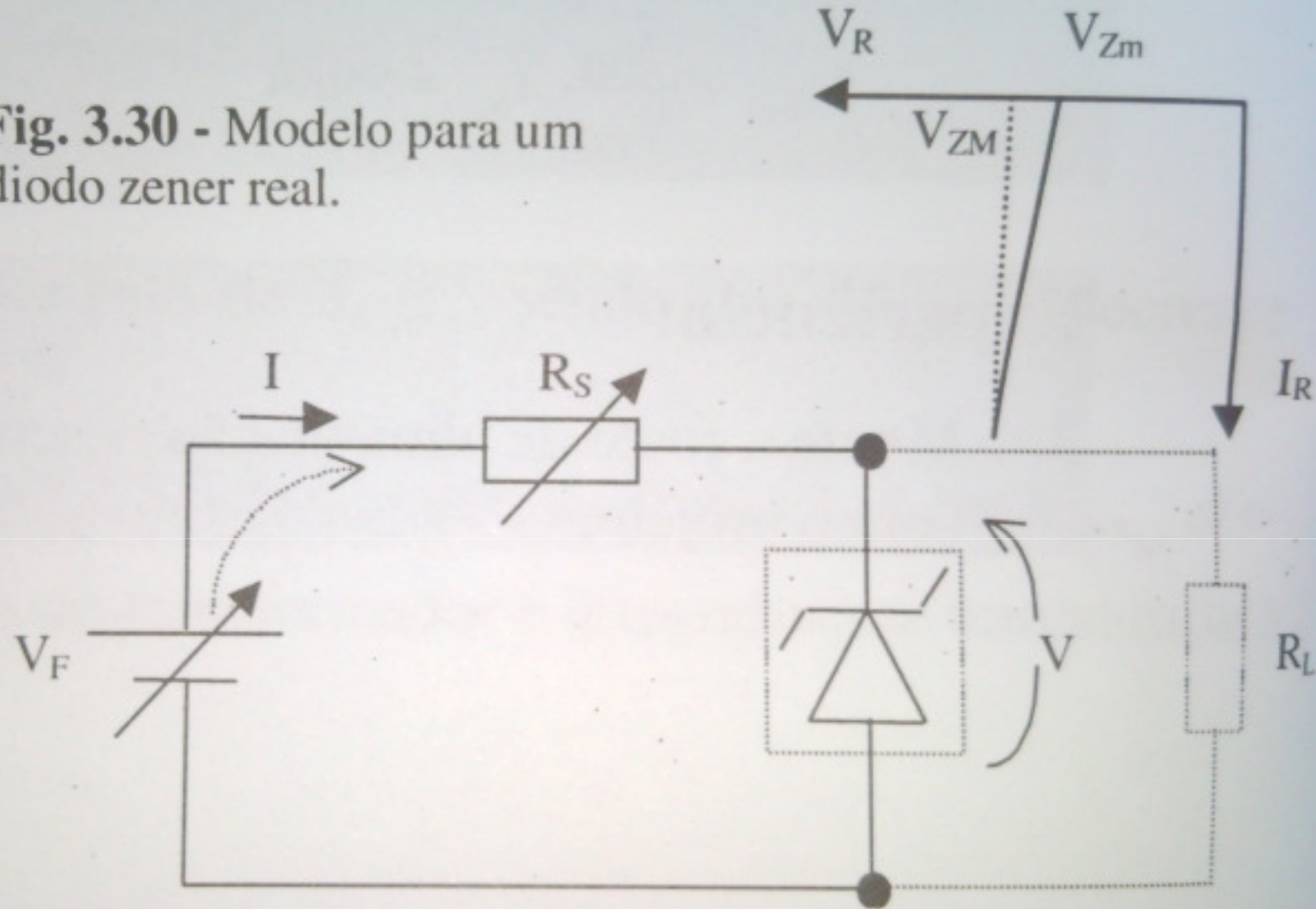


Fig. 3.31 - R_S é a resistência de segurança e pode incluir a resistência interna da fonte.

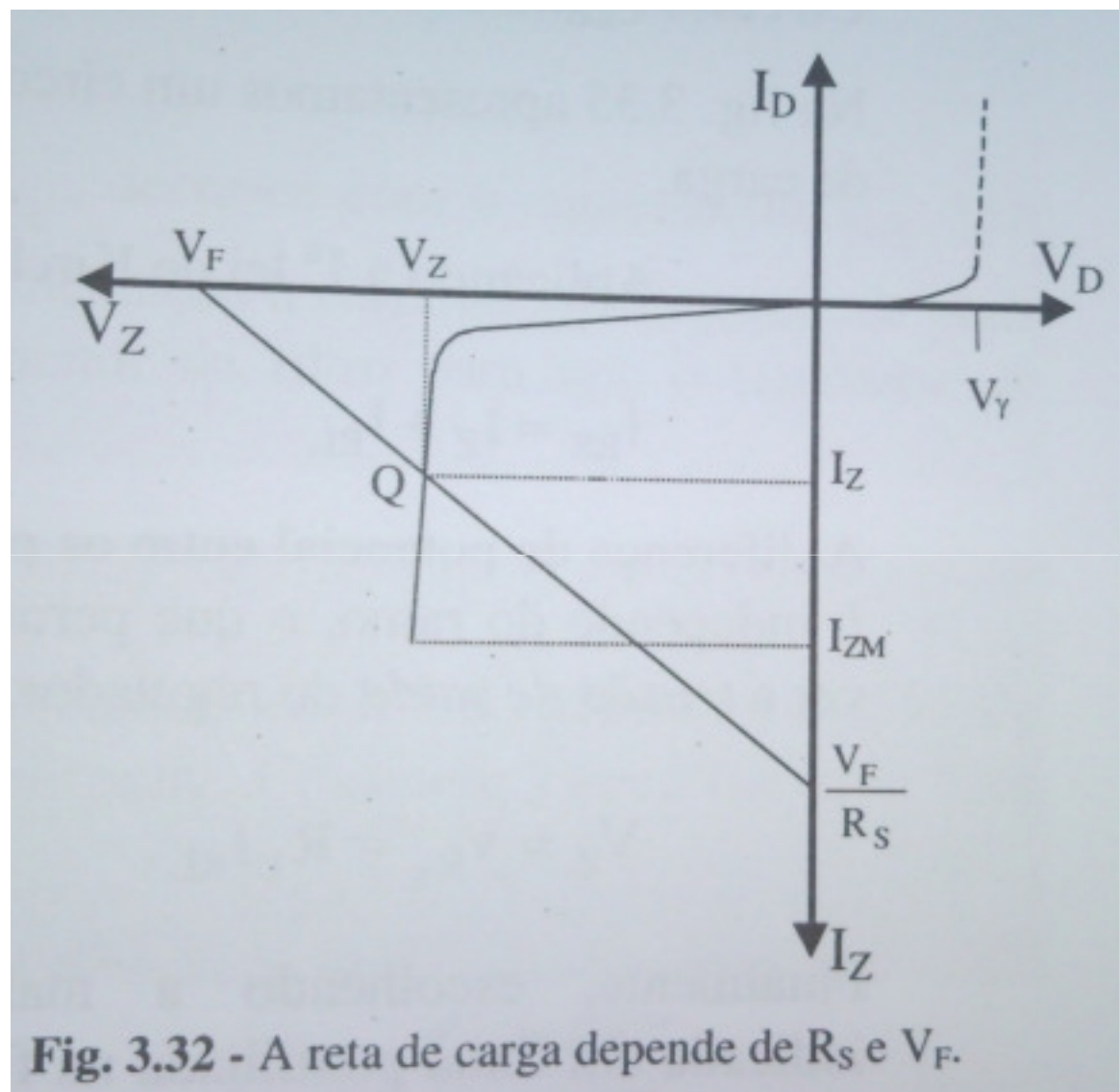


Fig. 3.32 - A reta de carga depende de R_S e V_F .

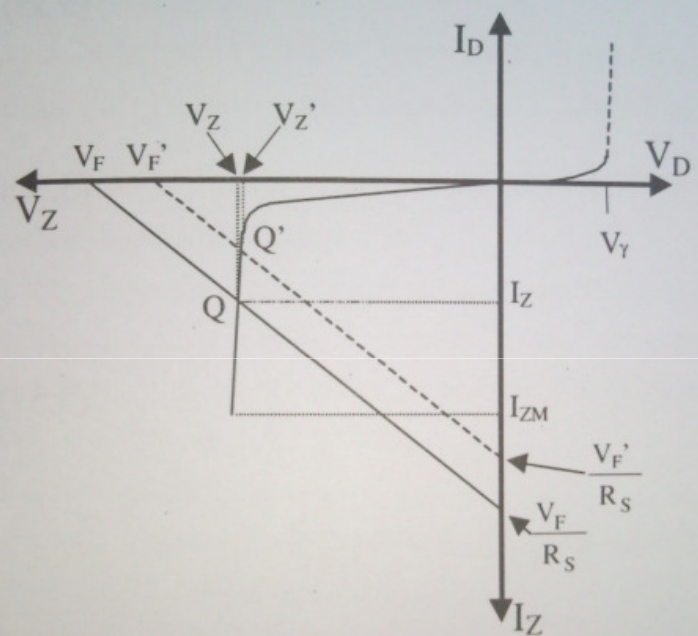


Fig. 3.33 - Comportamento do diodo zener quando ocorre uma variação da tensão da fonte.

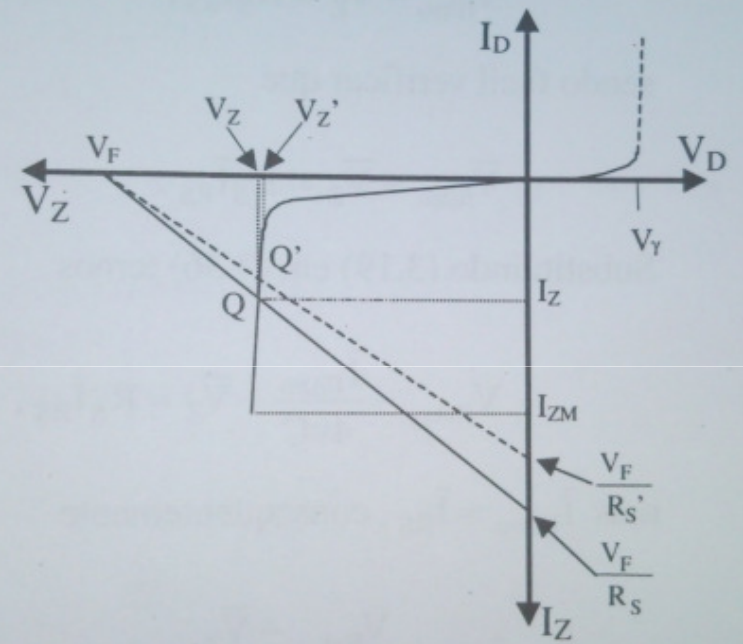


Fig. 3.34 - Comportamento do diodo zener quando ocorre uma variação da resistência de carga.

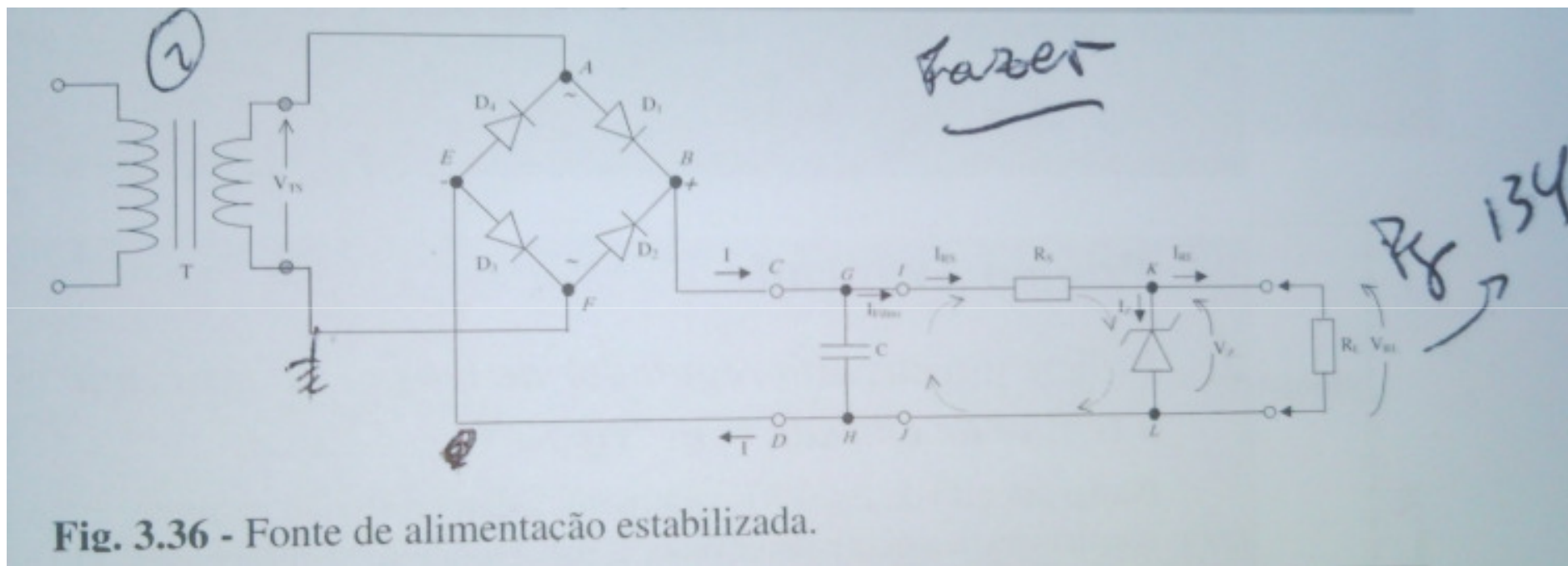


Fig. 3.36 - Fonte de alimentação estabilizada.